



15NM65-U2

Power MOSFET

15A, 650V N-CHANNEL SUPER-JUNCTION MOSFET

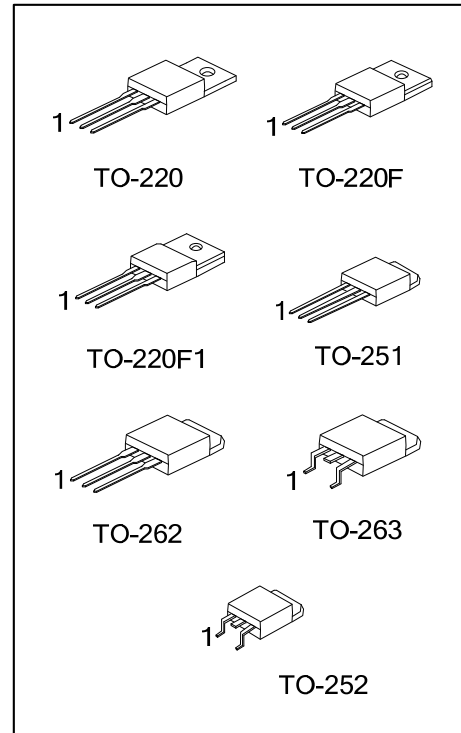
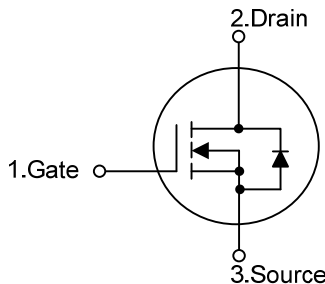
■ DESCRIPTION

The **UTC 15NM65-U2** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at AC-DC converters for power applications.

■ FEATURES

- * $R_{DS(ON)} \leq 0.43 \Omega @ V_{GS}=10V, I_D=7.5A$
- * By using Super Junction Structure
- * Fast Switching
- * With 100% Avalanche Tested

■ SYMBOL



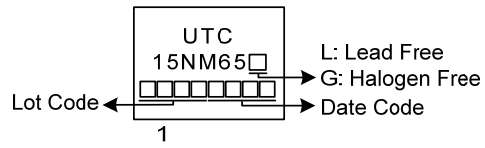
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
15NM65L-TA3-T	15NM65G-TA3-T	TO-220	G	D	S	Tube
15NM65L-TF3-T	15NM65G-TF3-T	TO-220F	G	D	S	Tube
15NM65L-TF1-T	15NM65G-TF1-T	TO-220F1	G	D	S	Tube
15NM65L-TM3-T	15NM65G-TM3-T	TO-251	G	D	S	Tube
15NM65L-TN3-R	15NM65G-TN3-R	TO-252	G	D	S	Tape Reel
15NM65L-T2Q-T	15NM65G-T2Q-T	TO-262	G	D	S	Tube
15NM65L-TQ2-T	15NM65G-TQ2-T	TO-263	G	D	S	Tube
15NM65L-TQ2-R	15NM65G-TQ2-R	TO-263	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>15NM65G-TA3-T</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Green Package</p>	<p>(1) T: Tube, R: Tape Reel</p> <p>(2) TA3: TO-220, TF1: TO-220F1, TF3: TO-220F TM3: TO-251, TN3: TO-252, T2Q: TO-262 TQ2: TO-263</p> <p>(3) G: Halogen Free and Lead Free, L: Lead Free</p>
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■ MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	± 30	V
Continuous Drain Current	Continuous	I_D	15	A
Pulsed Drain Current	Pulsed (Note 2)	I_{DM}	30	A
Avalanche energy	Single Pulsed (Note 3)	E_{AS}	163	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	2.3	V/nS
Power Dissipation	TO-220/TO-262	P_D	94	W
	TO-263			
	TO-220F/TO-220F1			
	TO-251/TO-252			
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature Range		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L=30\text{mH}$, $I_{AS}=3.3\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\Omega$, Starting $T_J = 25^\circ\text{C}$.

4. $I_{SD} \leq 15\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_J = 25^\circ\text{C}$.

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-220F	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
	TO-220F1/TO-262			
	TO-263			
	TO-251/TO-252			
Junction to Case	TO-220/TO-262	θ_{JC}	1.32	$^\circ\text{C}/\text{W}$
	TO-263			
	TO-220F/TO-220F1			
	TO-251/TO-252			

Note: Device mounted on FR-4 substrate P_C board, 2oz copper, with 1inch square copper plate.

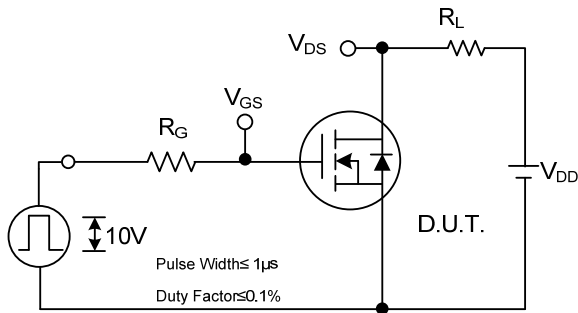
■ ELECTRICAL CHARACTERISTICS (T_J =25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} =0V, I _D =250μA	650			V	
Drain-Source Leakage Current		I _{DSS}	V _{DS} =650V, V _{GS} =0V			10	μA	
Gate-Source Leakage Current	Forward	I _{GSS}	V _{DS} =0V, V _{GS} =+30V			+100	nA	
	Reverse		V _{DS} =0V, V _{GS} =-30V			-100	nA	
ON CHARACTERISTICS								
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} = V _{GS} , I _D =250μA	2.5		4.5	V	
Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =7.5A			0.43	Ω	
DYNAMIC PARAMETERS								
Input Capacitance		C _{ISS}	V _{GS} =0V, V _{DS} =50V, f=1.0MHz		940		pF	
Output Capacitance		C _{OSS}				85		pF
Reverse Transfer Capacitance		C _{RSS}				4		pF
SWITCHING PARAMETERS								
Total Gate Charge (Note 1)		Q _G	V _{DS} =520V, V _{GS} =10V, I _D =15A (Note 1, 2)		39		nC	
Gate to Source Charge		Q _{GS}				11		nC
Gate to Drain Charge		Q _{GD}				13		nC
Turn-on Delay Time (Note 1)		t _{D(ON)}	V _{DD} =100V, V _{GS} =10V, I _D =15A, R _G =25Ω (Note 1, 2)		10		ns	
Rise Time		t _R				21		ns
Turn-off Delay Time		t _{D(OFF)}				105		ns
Fall-Time		t _F				43		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS								
Maximum Body-Diode Pulsed Current		I _S				15	A	
Drain-Source Diode Forward Voltage (Note 1)		I _{SM}				30	A	
Maximum Body-Diode Continuous Current		V _{SD}	I _S =15A, V _{GS} =0V			1.4	V	
Reverse Recovery Time (Note 1)		t _{rr}	I _S =15A, V _{GS} =0V, dI _F /dt=100A/μs		364		ns	
Reverse Recovery Charge		Q _{rr}				5		μC

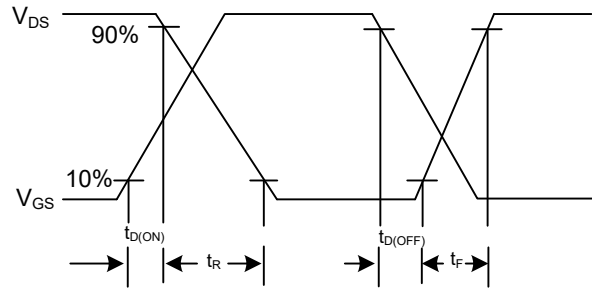
Note: 1. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%

2. Essentially independent of operating temperature

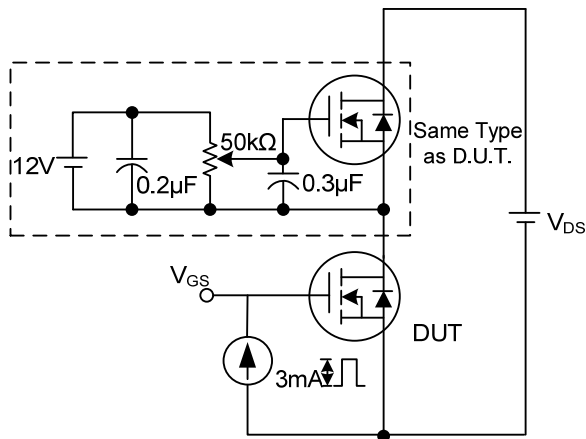
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



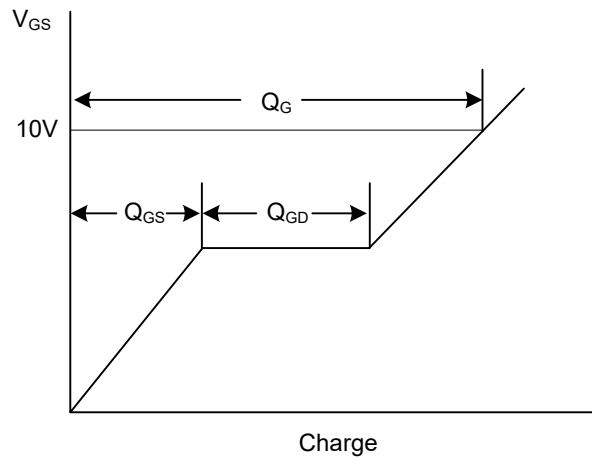
Switching Test Circuit



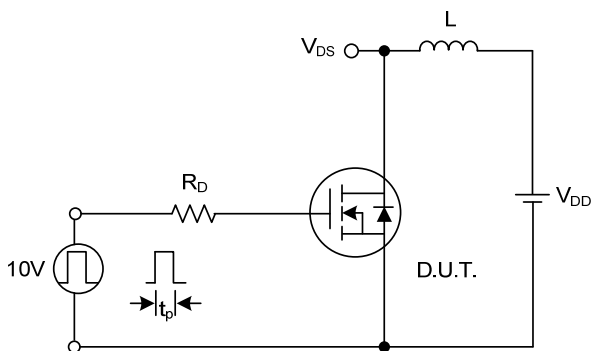
Switching Waveforms



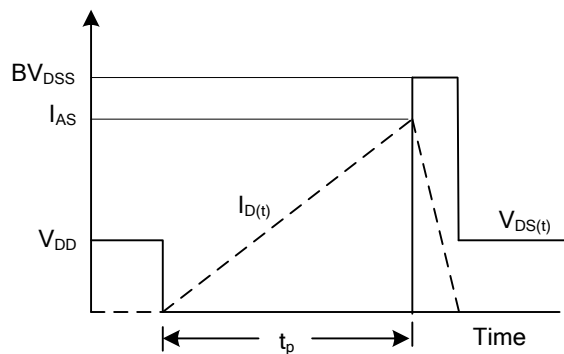
Gate Charge Test Circuit



Gate Charge Waveform

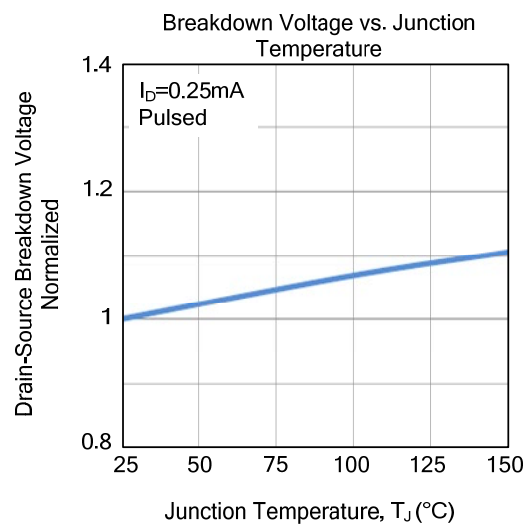
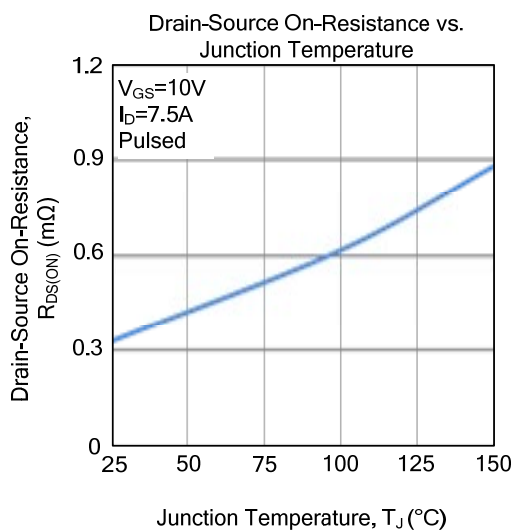
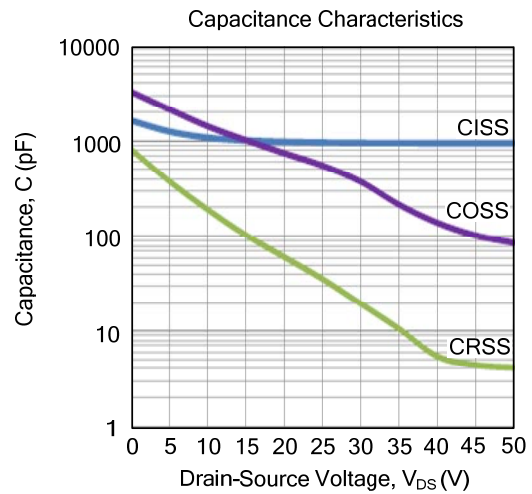
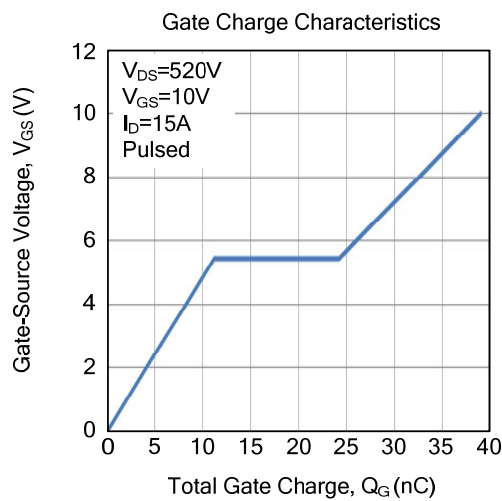
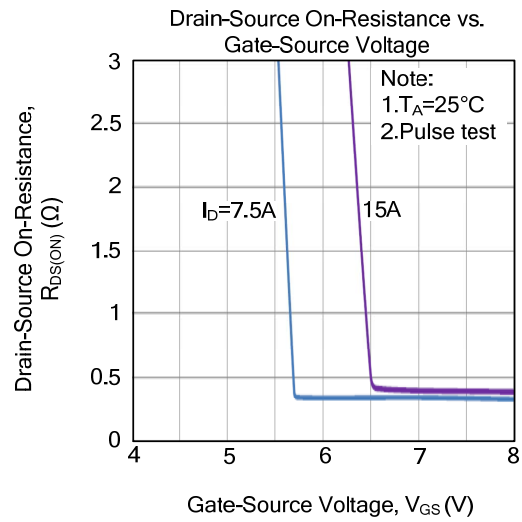
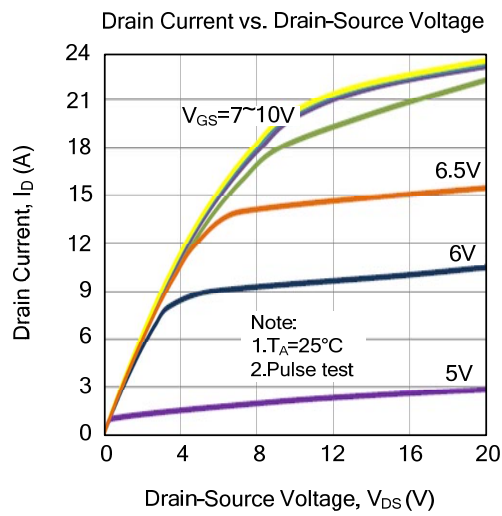


Unclamped Inductive Switching Test Circuit

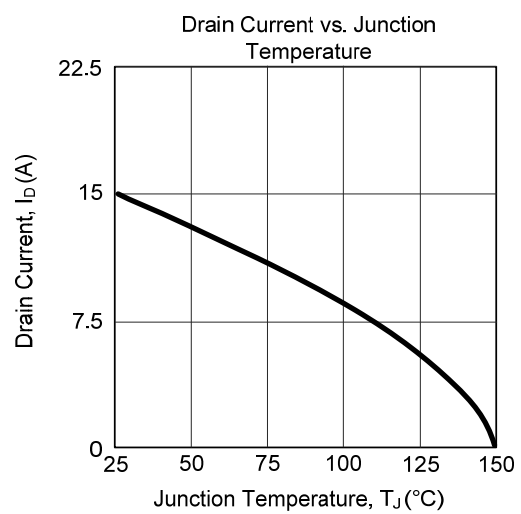
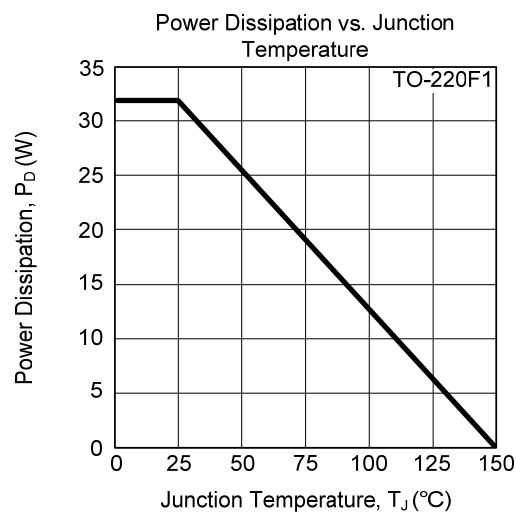
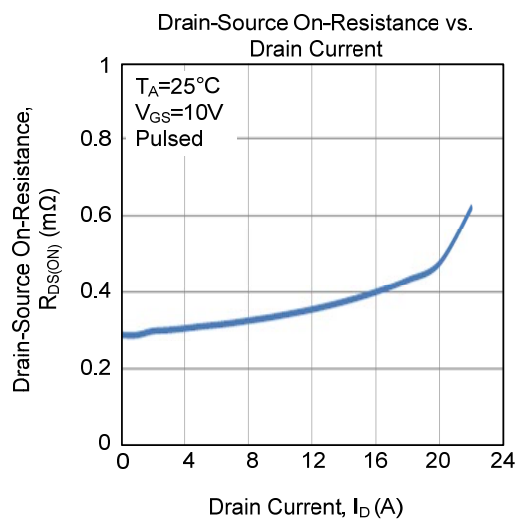
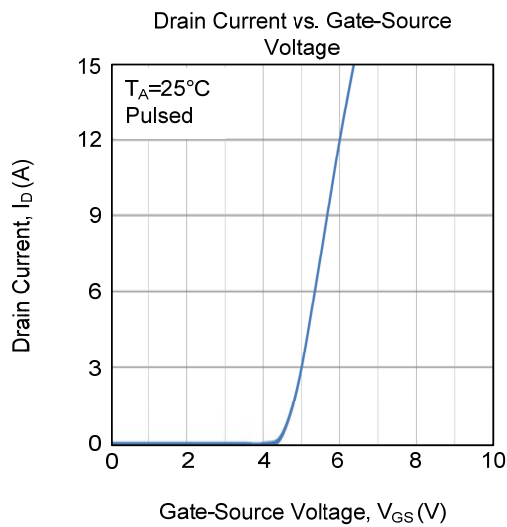
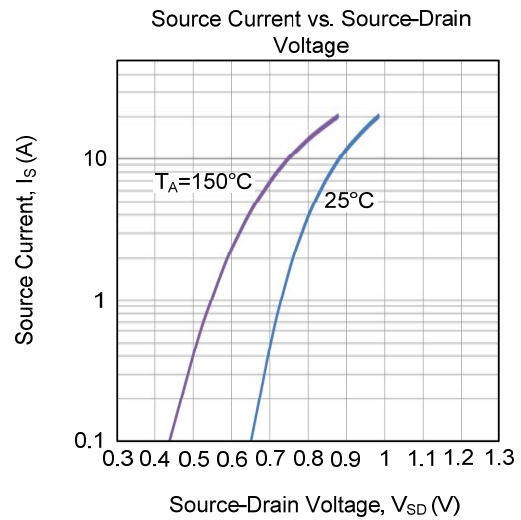
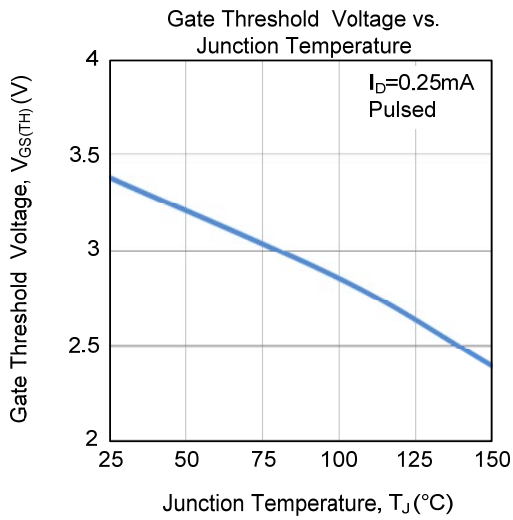


Unclamped Inductive Switching Waveforms

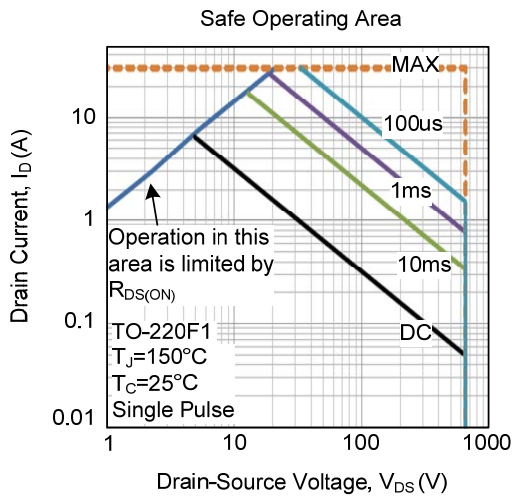
TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)



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